

“Tensile strained Ge tunnel field-effect transistors: k $\cdot$ p material modeling and numerical device simulation”. Kao K-H, Verhulst AS, Van de Put M, Vandenberghe WG, Sorée B, Magnus W, De Meyer K, Journal of applied physics **115**, 044505 (2014). <http://doi.org/10.1063/1.4862806>